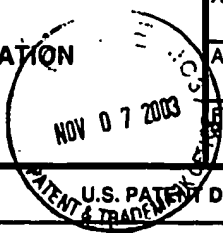


INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



ATTY DOCKET NO.
50033-00006

SERIAL NO.
10/630,238

APPLICANT(S)
Van Zeghbroeck, et al

FILING DATE
July 30, 2003

GROUP
1765

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
LV	a.	H1637	03/04/1997	Offord et al	437	173	
	b.	4,945,394	07/31/1990	Palmour et al	357	34	
	c.	5,266,503	11/30/1993	Wang et al	437	24	
	d.	6,180,958	01/30/2001	Cooper, Jr.	257	77	
	e.	6,181,200	01/30/2001	Titizian et al	330	66	
	f.	6,303,475	10/16/2001	Suvorov et al	438	519	
	g.	6,313,482	11/06/2001	Baliga	257	77	
	h.	6,323,506	11/27/2001	Alok	257	77	
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LV	k.	6,218,254	04/17/2001	Singh et al	438	364	

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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

LV		l.	Article entitled "Silicon Carbide Bipolar Transistor" by W. V. Munch and P. Hoeck published in <i>Solid State Electronics</i> , 1978, Vol. 21, pp. 479-480, Pergamon Press, Great Britain
LV		m.	Excerpt from textbook <i>Volume V Introduction to Microelectronic Fabrication</i> , pp. 71-73, author Richard C. Jaeger, Auburn University, published by Addison-Wesley Publishing Company, reprinted with corrections May, 1993.

EXAMINER

LAN VINH

DATE CONSIDERED

7/26/03

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NOV 07 2003

Docket Number (Optional)

50033-00006

Application Number

10/630,238

Applicant(s)

VAN ZEGHBROECK et al

Filing Date

July 30, 2003

Group Art Unit

1765

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
LV	n.	5,914,611	06/22/1999	Cheng	324	719	
LV	o.	6,228,665	05/08/2001	Griffith et al	438	14	

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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

LV	p.	U. S. Patent Application Serial No. 10/360,662, filed on February 7, 2003, entitled "Method of Fabricating Self-Aligned Silicon Carbide Semiconductor Devices", and further identified as Attorney Docket No. 50033-00005
LV	q.	U. S. Patent Application Serial No. 10/339,040, filed on January 9, 2003, entitled "Silicon Carbide Semiconductor Devices with a Regrown Contact Layer", and further identified as Attorney Docket No. 50033-00004.

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